

Technical Data Data Sheet N1193, Rev. B

Green Products

220CMQ025 SCHOTTKY RECTIFIER

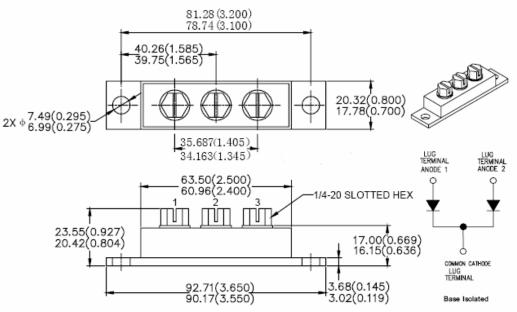
Applications:

- Parallel switching power supply Free-Wheeling diodes Reverse battery protection
- Converters
 Redundant power subsystems

Features:

- 150[°]C T_J operation
- Center tap module
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm/Inches



Please Note: Anode 1 = Terminal 1; Anode 2 = Terminal 3; Common Cathode = Terminal 2 Suffix R Denotes for Reversed Polarity.

PRM4 (Isolated)

MARKING,MOLDING RESIN Marking for 220CMQ025, 1st row SS YYWWL, 2nd row 220CMQ025 Where YY is the manufacture year WW is the manufacture week code L is the wafer's Lot Number Molding resin Epoxy resin UL:94V-0

Weiqi Street, Airport Development Zone, Jiangning District, Nanjing, China 211113 (86) 25-87123907 •
FAX (86) 25-87123900 • World Wide Web Site - http://www.sangdest.com.cn • E-Mail Address - sales@ sangdest.com.cn •



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Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units	
Peak Inverse Voltage	V _{RWM}	-	25		V	
Max. Average Forward	1	50% duty cycle @T _c =74°C, rectangular wave form	110	per leg	А	
	F(AV)		220	per device	А	
Max. Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse		2850	A	

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V _{F1}	@ 110A, Pulse, T _J = 25 °C	0.48	V
	V _{F2}	@ 110A, Pulse, T _J = 125 °C	0.40	V
Max. Reverse Current at DC condition	I _{R1}	$@V_R = rated V_R$ T _J = 25 °C	10	mA
Max. Reverse Current	I _{R2}	$@V_R = rated V_R$ T _J = 125 °C	560	mA
Max. Junction Capacitance	CT	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	7400	pF
Typical Series Inductance (per leg)	L _S	Measured lead to lead 5 mm from package body	7.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/µs

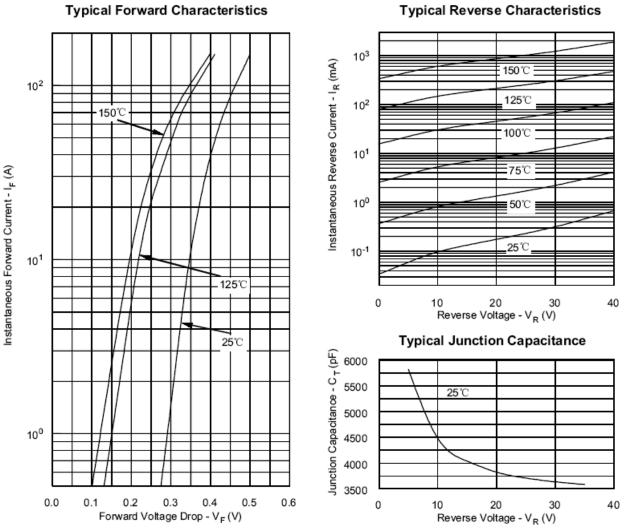
* Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specifi	Units		
Max. Junction Temperature	TJ	-	-55 to	°C		
Max. Storage Temperature	T _{stg}	-	-55 to	°C		
Maximum Thermal Resistance Junction to Case (per leg)	$R_{ ext{ heta}JC}$	DC operation	0.70		°C/W	
Maximum Thermal Resistance Junction to Case (per device)	R _{θJC}	DC operation	0.35		°C/W	
Typical Thermal Resistance, case to Heat Sink	$R_{\theta cs}$	Mounting surface, smooth and greased	0.10		°C/W	
Mounting Torque	Тм	-	Mounting Torque Terminal Torque	24(min) 35(max) 35(min) 46(max)	Kg-cm	
Approximate Weight	wt	-	79		g	
Case Style	PRM4 (Isolated)					



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Typical Reverse Characteristics

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